

### Description

The DGTD65T50S1PT is produced using advanced Field Stop Trench IGBT Technology, which provides excellent quality and high-switching performance.

### Features

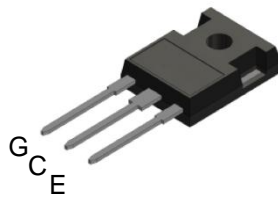
- High-Speed Switching & Low Power Loss
- $V_{CE(sat)} = 1.85V @ I_C = 50A$
- High Input Impedance
- $t_{rr} = 80ns$  (typ) @  $di_f/dt = 1000A/\mu s$
- $E_{off} = 0.55mJ @ T_C = 25^\circ C$
- Maximum Junction Temperature  $175^\circ C$
- **Lead-Free Finish & RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

### Applications

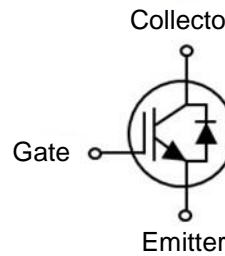
- UPS
- Welder
- Solar Inverter
- IH Cooker

### Mechanical Data

- Case: TO-247 (Type MC)
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Terminals: Finish – Matte Tin Plated Leads.  
Solderable per MIL-STD-202, Method 208 <sup>(E3)</sup>
- Weight: 5.6 grams (Approximate)



TO-247



Device Symbol

### Ordering Information (Note 4)

Product	Marking	Quantity
DGTD65T50S1PT	DGTD65T50S1	450 per Box in Tubes (Note 5)

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.
  5. 30 Devices per Tube.

### Marking Information



$\text{D}||$  = Manufacturer's Marking  
 DGTD65T50S1 = Product Type Marking Code  
 YY = Year (ex: 18 = 2018)  
 LLLLL = Lot Code  
 WW = Week (01 to 53)

**Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CE</sub>	650	V
DC Collector Current, limited by T <sub>vjmax</sub>	I <sub>C</sub>	T <sub>C</sub> = 25°C	100
		T <sub>C</sub> = 100°C	50
Pulsed Collector Current, t <sub>p</sub> limited by T <sub>vjmax</sub>	I <sub>Cpuls</sub>	200	A
Turn Off Safe Operating Area V <sub>CE</sub> ≤ 650V, T <sub>vj</sub> = 175°C	-	200	A
Diode Forward Current limited by T <sub>vjmax</sub>	I <sub>F</sub>	T <sub>C</sub> = 25°C	60
		T <sub>C</sub> = 100°C	30
Diode Pulsed Current, t <sub>p</sub> limited by T <sub>vjmax</sub>	I <sub>Fpuls</sub>	200	A
Gate-Emitter Voltage	V <sub>GE</sub>	±20	V
Short Circuit Withstand Time V <sub>CC</sub> ≤ 400V, V <sub>GE</sub> = 15V, T <sub>vj</sub> = 150°C Allowed Number of Short Circuits < 1000 Time Between Short Circuits ≥ 1.0s	tsc	5	μs

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

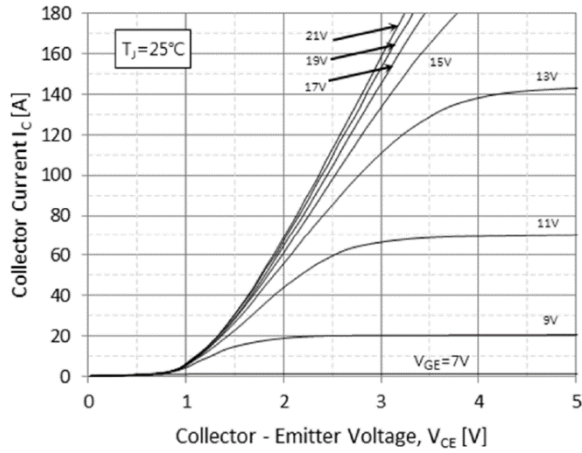
Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor (Note 6)	P <sub>D</sub>	T <sub>C</sub> = 25°C	375
		T <sub>C</sub> = 100°C	188
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	40	°C/W
Thermal Resistance, Junction to Case for IGBT (Note 6)	R <sub>θJC</sub>	0.40	
Thermal Resistance, Junction to Case for Diode (Note 6)	R <sub>θJC</sub>	1.20	
Operating Temperature	T <sub>vj</sub>	-40 to +175	°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	

Note: 6. When mounted on a standard JEDEC 2-layer FR-4 board.

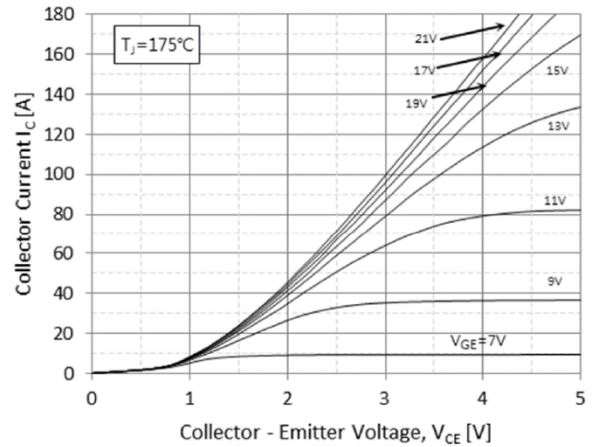
**Electrical Characteristics** (@ $T_{vj} = +25^{\circ}\text{C}$ , unless otherwise specified.)

Parameter	Symbol	Min	Typ	Max	Unit	Condition	
<b>STATIC CHARACTERISTICS</b>							
Collector-Emitter Breakdown Voltage	$BV_{CES}$	650	–	–	V	$I_C = 2\text{mA}, V_{GE} = 0\text{V}$	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$T_{vj} = 25^{\circ}\text{C}$	–	1.85	2.40	V	$I_C = 50\text{A}, V_{GE} = 15\text{V}$
		$T_{vj} = 175^{\circ}\text{C}$	–	2.20	–		
Diode Forward Voltage	$V_F$	$T_{vj} = 25^{\circ}\text{C}$	–	1.65	2.05	V	$V_{GE} = 0\text{V}, I_F = 30\text{A}$
		$T_{vj} = 175^{\circ}\text{C}$	–	1.55	–		
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	3.8	5.0	6.2	V	$V_{CE} = V_{GE}, I_C = 0.5\text{mA}$	
Zero Gate Voltage Collector Current	$I_{CES}$	–	–	40	$\mu\text{A}$	$V_{CE} = 650\text{V}, V_{GE} = 0\text{V}$	
Gate-Emitter Leakage Current	$I_{GES}$	–	–	$\pm 100$	nA	$V_{GE} = 20\text{V}, V_{CE} = 0\text{V}$	
<b>DYNAMIC CHARACTERISTICS</b>							
Total Gate Charge	$Q_g$	–	287	–	nC	$V_{CE} = 520\text{V}, I_C = 50\text{A}, V_{GE} = 15\text{V}$	
Gate-Emitter Charge	$Q_{ge}$	–	42	–			
Gate-Collector Charge	$Q_{gc}$	–	181	–			
Input Capacitance	$C_{ies}$	–	4,453	–	pF	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$	
Reverse Transfer Capacitance	$C_{res}$	–	161	–			
Output Capacitance	$C_{oes}$	–	238	–			
Internal Emitter Inductance Measured 5mm (0.197") From Case	$L_E$	–	13	–	nH	–	
Short Circuit Collector Current Max. 1000 Short Circuits. Time Between Short Circuits $\geq 1.0\text{s}$	$I_{C(SC)}$	–	140	–	A	$V_{GE} = 15\text{V}, V_{CC} = 400\text{V}, t_{SC} \leq 5\mu\text{s}, T_{vj} = 150^{\circ}\text{C}$	
<b>SWITCHING CHARACTERISTICS</b>							
Turn-on Delay Time	$t_{d(on)}$	–	58	–	ns	$V_{GE} = 15\text{V}, V_{CC} = 400\text{V}, I_C = 50\text{A}, R_G = 7.9\Omega, \text{Inductive Load}, T_{vj} = 25^{\circ}\text{C}$	
Rise time	$t_r$	–	60	–			
Turn-off Delay Time	$t_{d(off)}$	–	328	–			
Fall Time	$t_f$	–	44	–	mJ		
Turn-on Switching Energy	$E_{on}$	–	0.77	–			
Turn-off Switching Energy	$E_{off}$	–	0.55	–			
Total Switching Energy	$E_{ts}$	–	1.32	–	ns	$I_F = 30\text{A}, di_F/dt = 1000\text{A}/\mu\text{s}, T_{vj} = 25^{\circ}\text{C}$	
Reverse Recovery Time	$t_{rr}$	–	80	–			
Reverse Recovery Current	$I_{rr}$	–	24	–			A
Reverse Recovery Charge	$Q_{rr}$	–	0.95	–	$\mu\text{C}$		
Turn-on Delay Time	$t_{d(on)}$	–	51	–	ns		$V_{GE} = 15\text{V}, V_{CC} = 400\text{V}, I_C = 50\text{A}, R_G = 7.9\Omega, \text{Inductive Load}, T_{vj} = 175^{\circ}\text{C}$
Rise time	$t_r$	–	66	–			
Turn-off Delay Time	$t_{d(off)}$	–	350	–			
Fall Time	$t_f$	–	49	–	mJ		
Turn-on Switching Energy	$E_{on}$	–	1.05	–			
Turn-off Switching Energy	$E_{off}$	–	0.55	–			
Total Switching Energy	$E_{ts}$	–	1.6	–	ns	$I_F = 30\text{A}, di_F/dt = 1000\text{A}/\mu\text{s}, T_{vj} = 175^{\circ}\text{C}$	
Reverse Recovery Time	$t_{rr}$	–	116	–			
Reverse Recovery Current	$I_{rr}$	–	34	–			A
Reverse Recovery Charge	$Q_{rr}$	–	1.97	–	$\mu\text{C}$		

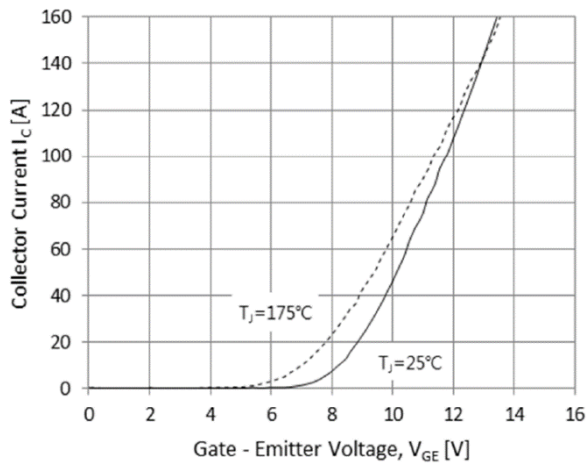
**Typical Performance Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)



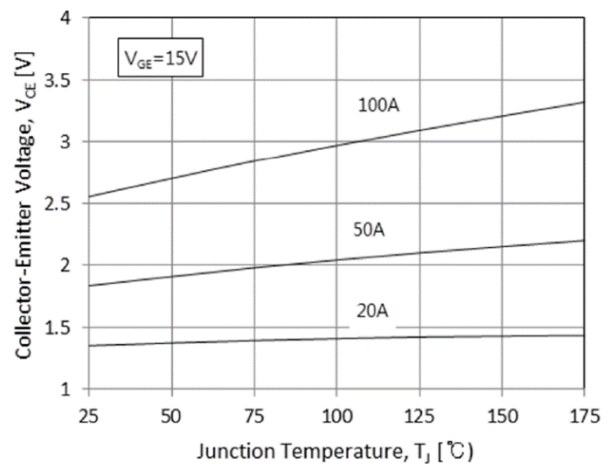
**Fig.1 Typical Output Characteristics ( $T_J = 25^\circ\text{C}$ )**



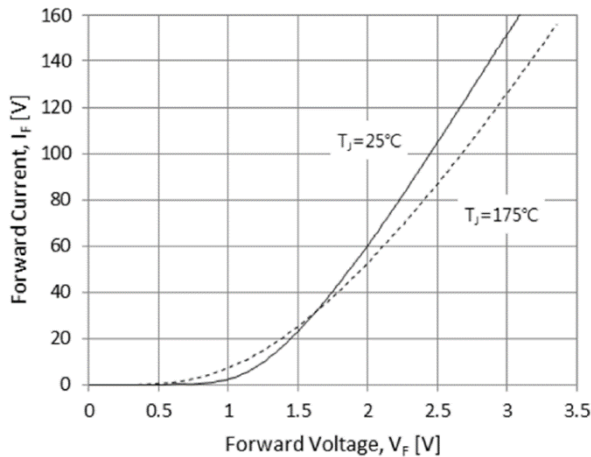
**Fig.2 Typical Output Characteristics ( $T_J = 175^\circ\text{C}$ )**



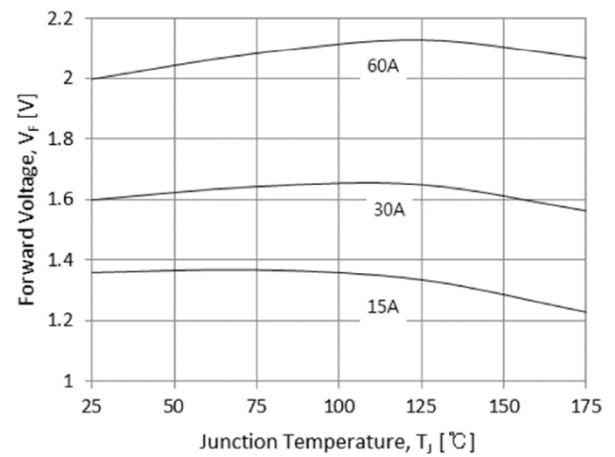
**Fig.3 Typical Transfer Characteristics**



**Fig.4 Typical Collector-Emitter Saturation Voltage - Junction Temperature**

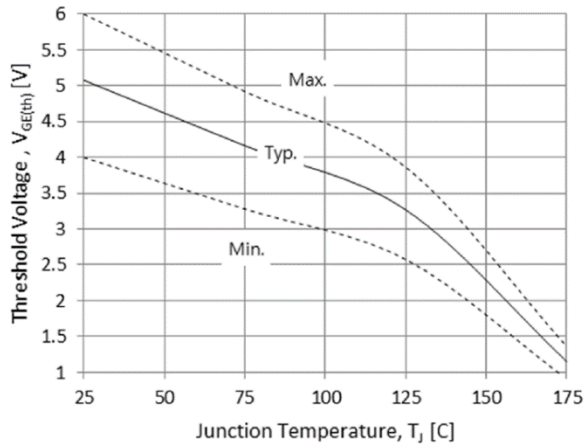


**Fig.5 Diode Forward Characteristics**

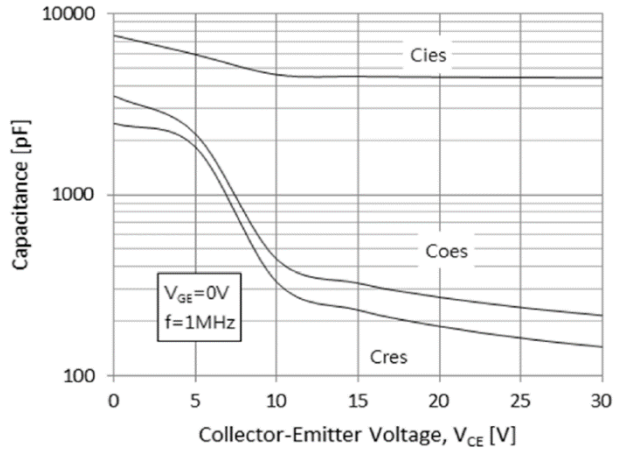


**Fig.6 Diode Forward-Junction Temperature**

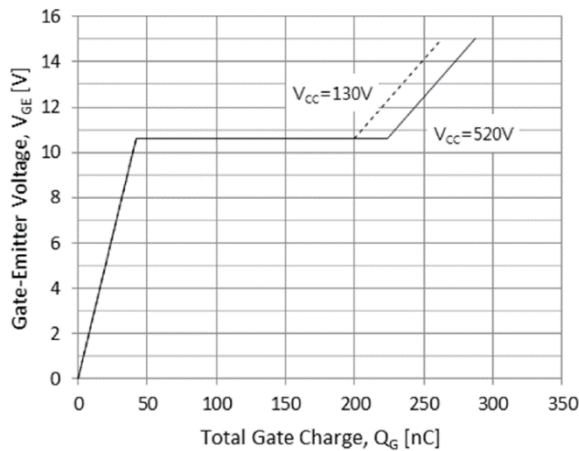
**Typical Performance Characteristics** (continued)



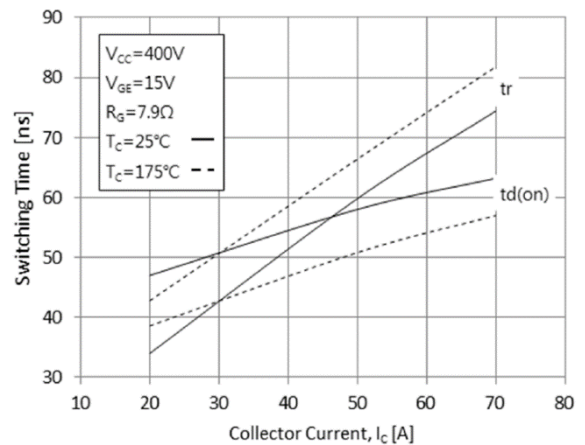
**Fig.7 Threshold Voltage-Junction Temperature**



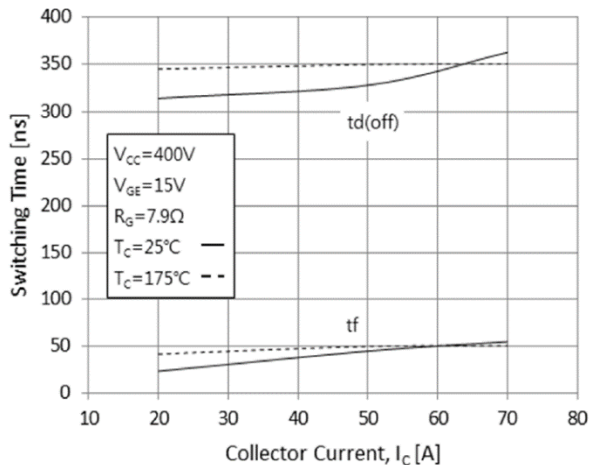
**Fig.8 Typical Capacitance**



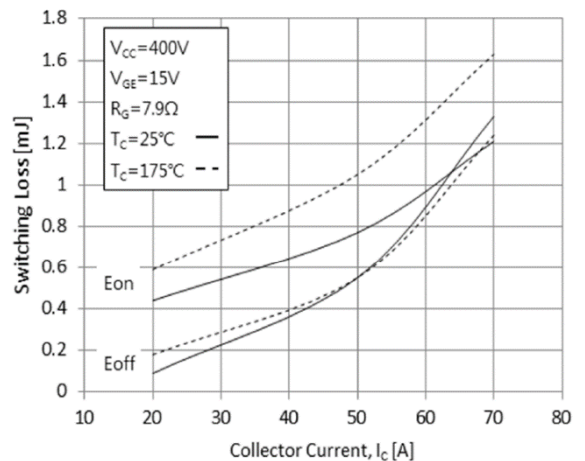
**Fig.9 Typical Gate Charge**



**Fig.10 Typical Turn on-Collector Current**

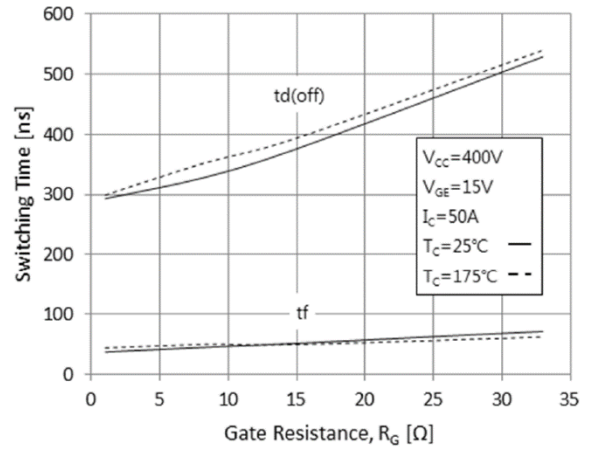
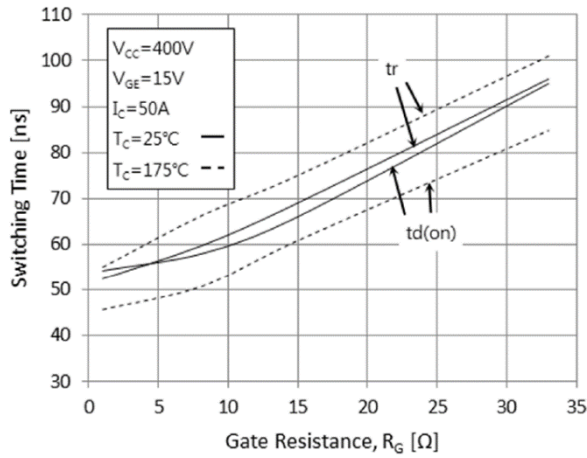


**Fig.11 Typical Turn off-Collector Current**



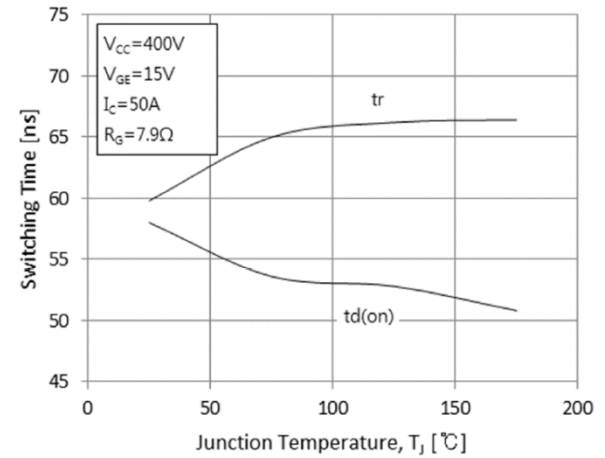
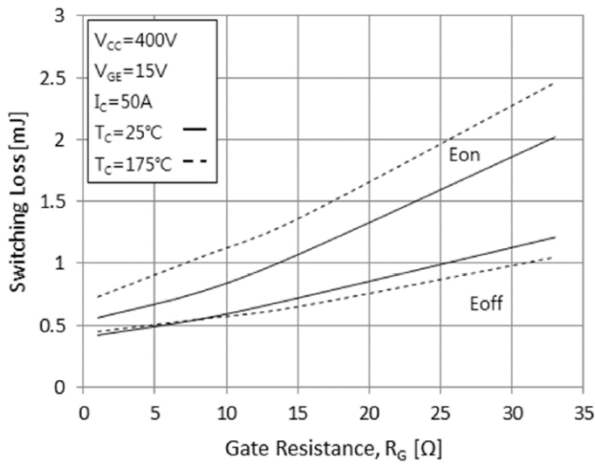
**Fig.12 Switching Loss-Collector Current**

**Typical Performance Characteristics (cont.)**



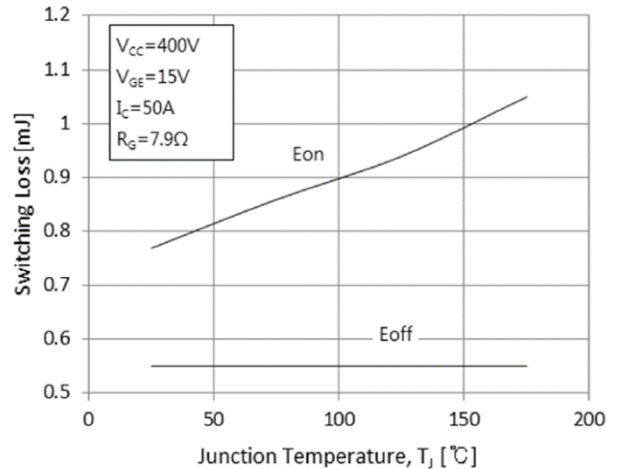
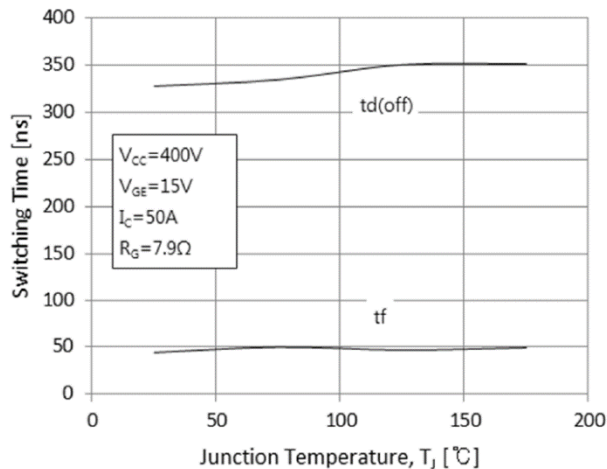
**Fig.13 Turn on Characteristics-Gate Resistance**

**Fig.14 Turn off Characteristics-Gate Resistance**



**Fig.15 Switching Loss-Gate Resistance**

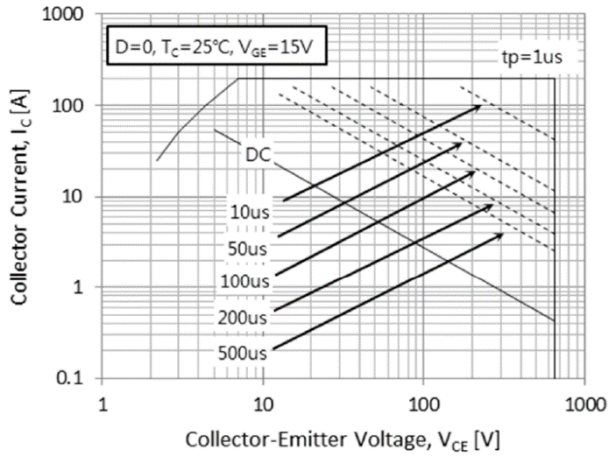
**Fig.16 Turn on Characteristics-Junction Temperature**



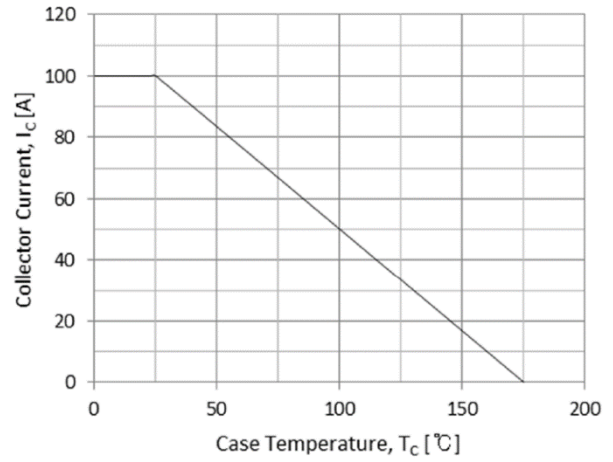
**Fig.17 Turn off Characteristics-Junction Temperature**

**Fig.18 Switching Loss-Junction Temperature**

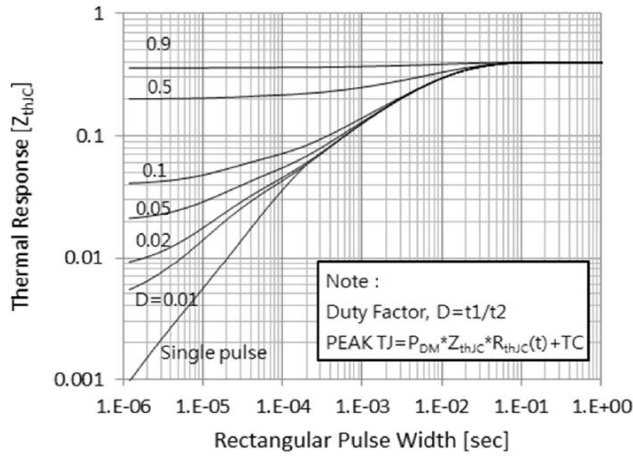
**Typical Performance Characteristics** (cont.)



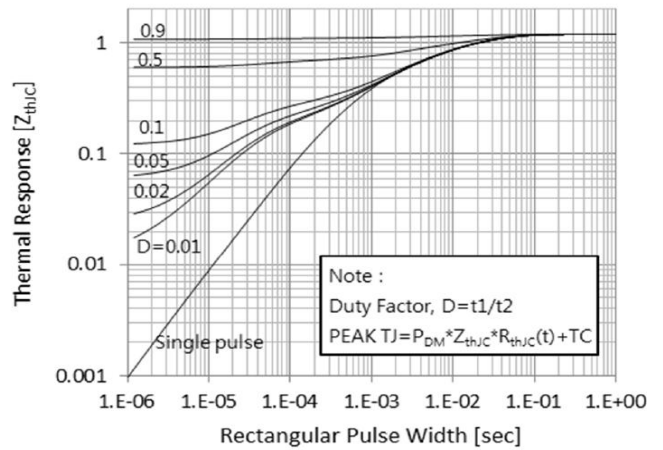
**Fig.19 Forward Bias Safe Operating Area**



**Fig.20 Case Temperature-Collector Current**



**Fig.21 IGBT Transient Thermal Impedance**

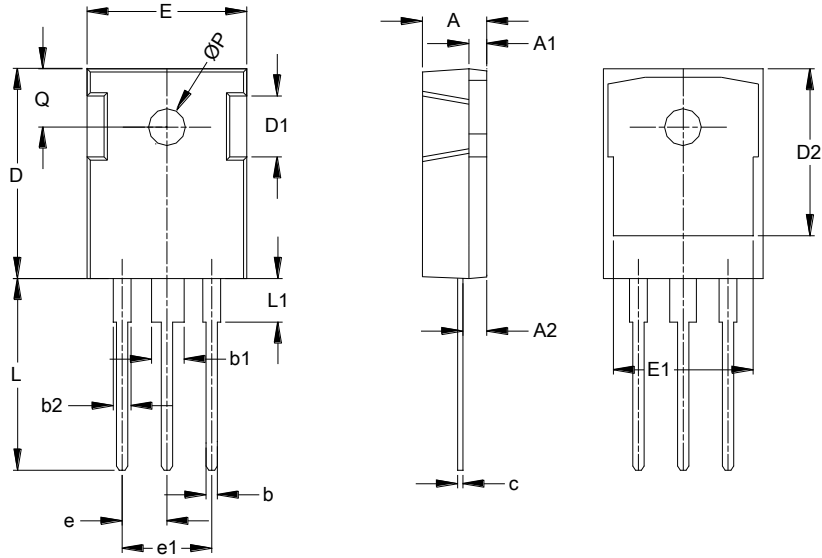


**Fig.22 FRD Transient Thermal Impedance**

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**TO-247 (Type MC)**



TO-247 (Type MC)			
Dim	Min	Max	Typ
A	4.700	5.310	-
A1	1.500	2.490	-
A2	2.200	2.600	-
b	0.990	1.400	-
b1	2.590	3.430	-
b2	1.650	2.390	-
c	0.380	0.890	-
D	20.30	21.46	-
D1	4.320	5.490	-
D2	13.08	-	-
E	15.45	16.26	-
E1	13.06	14.02	-
e	5.450		
e1	10.90		
L	19.81	20.57	-
L1	-	4.500	-
Q	5.380	6.200	-
øP	3.500	3.700	-
<b>All Dimensions in mm</b>			

Note : For high-voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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